

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-2.6	A
		T <sub>A</sub> = +70°C		-2	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-8	A

### Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)			R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range			T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-800	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
On-State Drain Current	I <sub>D(ON)</sub>	-6	—	—	A	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -4.5V
		-3	—	—		V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -2.5V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±80	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.45	—	-1.25	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	80	110	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.6A
		—	165	225		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	4	—	s	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.6A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	—	—	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.6A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iSS</sub>	—	250	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	88	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	58	—	pF	
Gate Resistance	R <sub>g</sub>	—	12	16	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	4.3	5.3	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -2.7A
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Repetitive rating, pulse width limited by junction temperature.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to production testing.

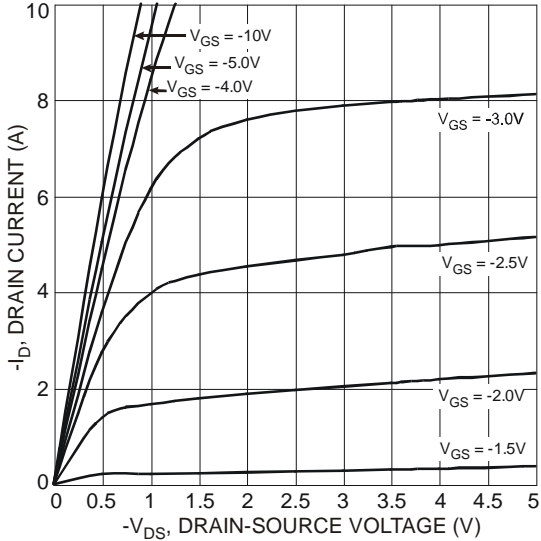


Figure 1 Typical Output Characteristics

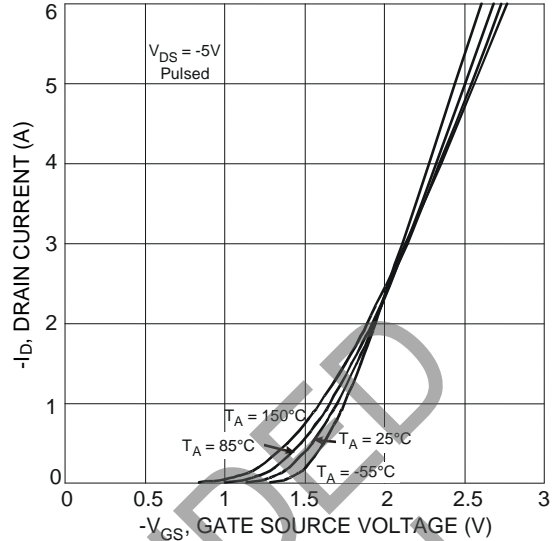


Figure 2 Typical Transfer Characteristics

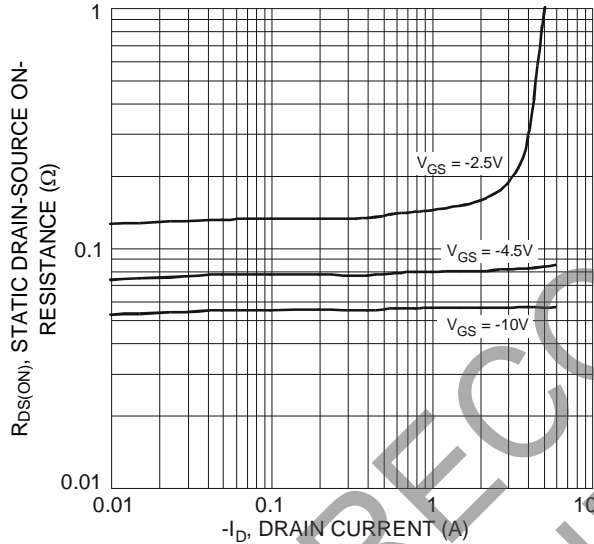


Figure 3 On-Resistance vs. Drain Current and Gate Voltage

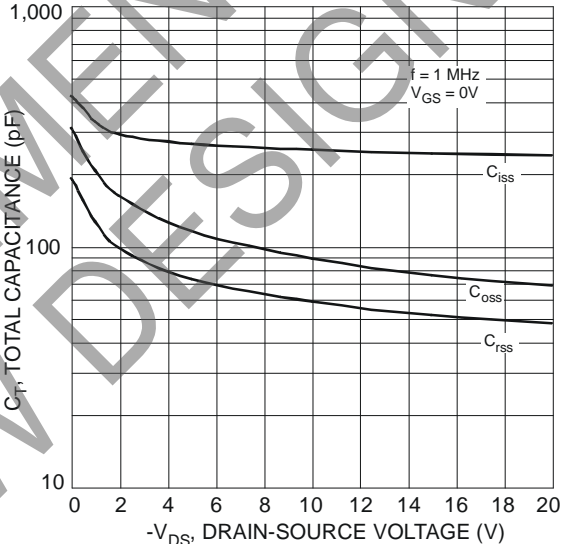


Figure 4 Typical Total Capacitance

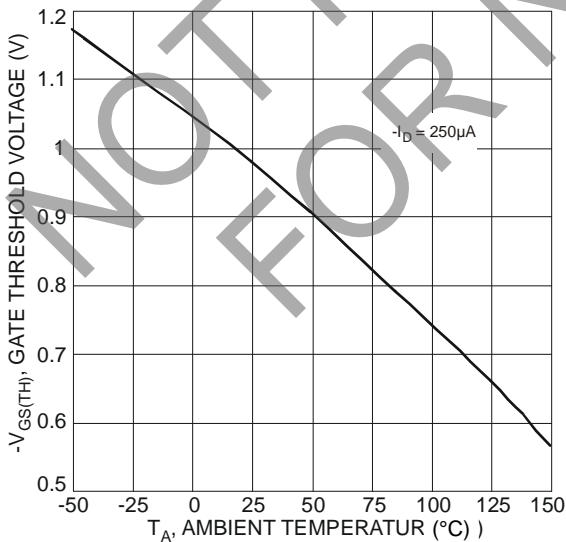


Figure 5 Gate Threshold Voltage vs. Ambient Temperature

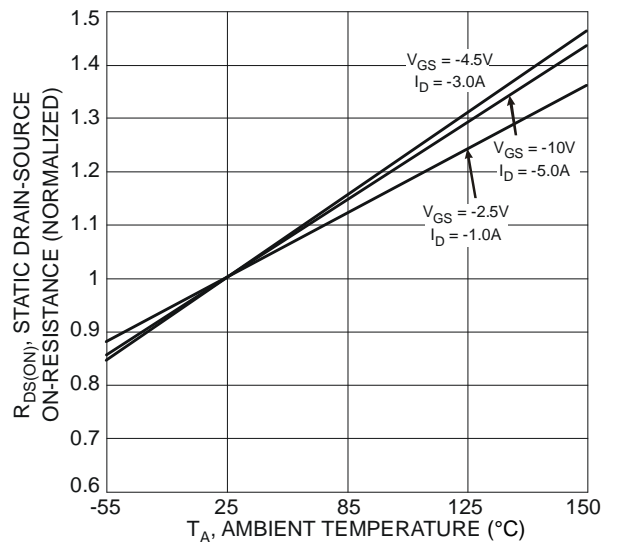


Figure 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

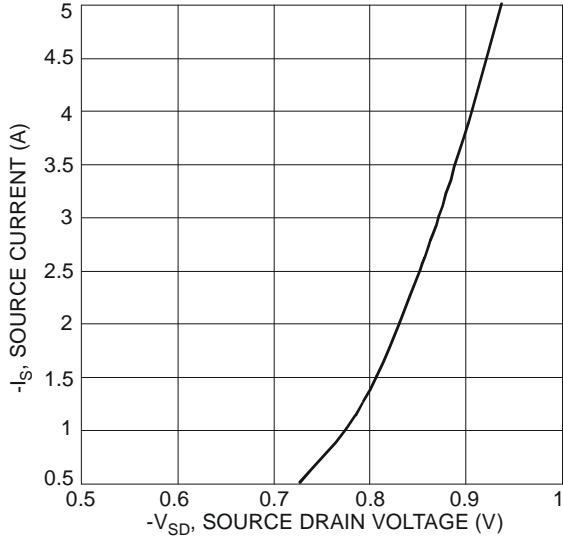


Figure 7 Reverse Drain Current vs. Source-Drain Voltage

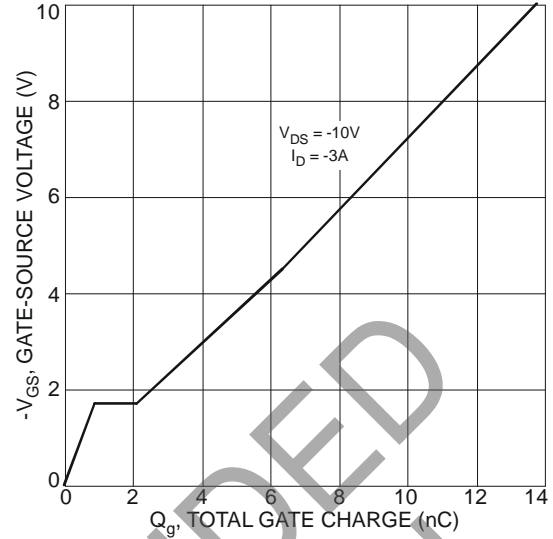


Figure 8 Gate-Charge Characteristics

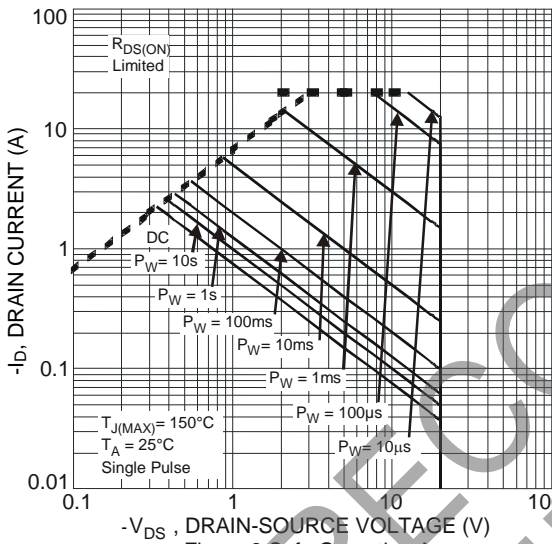


Figure 9 Safe Operation Area

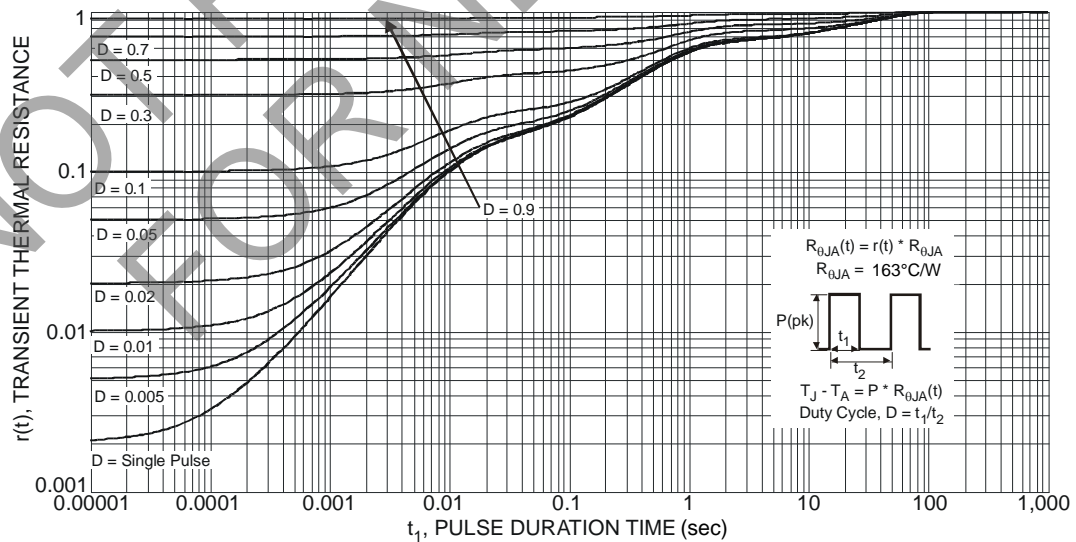
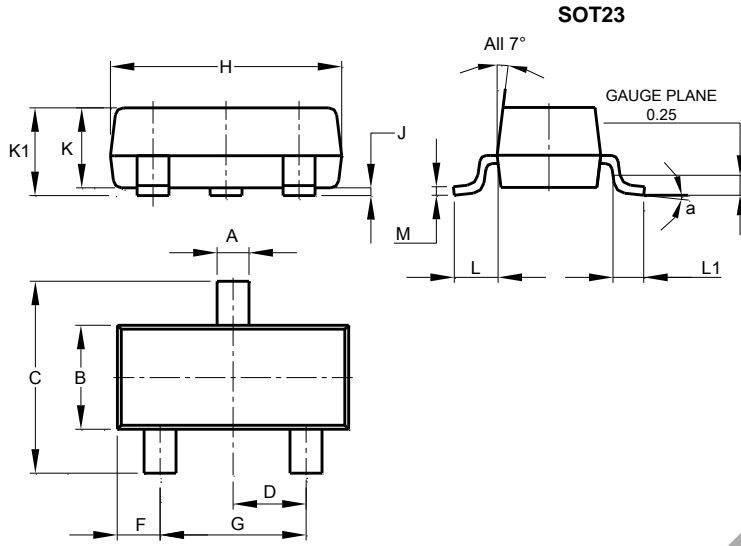


Figure 10 Transient Thermal Response

## Package Outline Dimensions

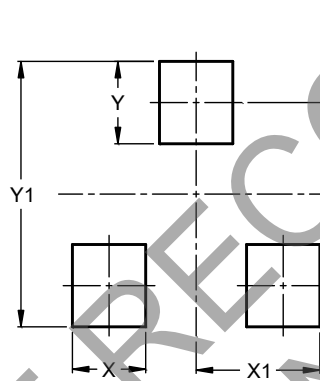
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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